

**In the Specification**

✓ On page 4, line 17, immediately after "substrate 12." insert ~~/~~As depicted, layer 16

D<sup>1</sup> is disposed on and in continuous contact with layer 14--.

✓ On page 5, line 12, replace "about 10-25" with --greater than about 25--.

✓ On page 6, line 4, replace "greater than about 25" with --about 25--.

On page 8, line 10, immediately after "and 36." insert ~~/~~As depicted, each floating

D<sup>2</sup> gate transistor has tunnel oxide 14 in continuous contact with first material 16, and is disposed over substrate 12 in a manner such that essentially none of tunnel oxide 14 overlies one of source regions 38, 40 or drain region 42--.

✓ **In the Drawing**

Please modify Fig. 8 as shown in the marked-up-in-red copy thereof included herewith.